

3CD8,3CD9,3CD010**PNP Silicon Low Frequency High Power Transistor****Features:**

1. Heavy output current.Small saturation voltage drop. Good temperature stability.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611.
3. Use for power amplify, Low-speed switch, power adjustment.
4. Quality Class: JP, JT, JCT, GS, G, G+.

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							
			3CD8		3CD9			3CD010		
			A	B	C	D	E	F	G	H
Collector-Emitter Voltage	V_{CEO}	V	30	50	80	110	150	200	250	300
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	30	50	80	110	150	200	250	300
			3CD8: $I_C=10mA$		3CD9: $I_C=10mA$			3CD010: $I_C=1mA$		
Emitter-Base Voltage	V_{EBO}	V	4		4			4		
Max. Collector Current	I_{CM}	A	10		15			1		
Max. Collector Dissipation	P_{CM}	W	100 ($T_c \leq 75^\circ C$)		150 ($T_c \leq 75^\circ C$)			10 ($T_c \leq 75^\circ C$)		
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
C-E Leakage Current	I_{CEO}	mA	2 ($V_{CE}=20V$)		3 ($V_{CE}=20V$)			1.0 ($V_{CE}=50V$)		
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	2		2			1.2		
			(A~E: $I_C=5A, I_B=1A$; F~H: $I_C=3A, I_B=0.6A$)		(A~E: $I_C=7.5A, I_B=1.5A$; F~H: $I_C=5A, I_B=1A$)			(A~E: $I_C=0.5A, I_B=0.1A$; F~H: $I_C=0.25A, I_B=0.05A$)		
DC Current Gain	h_{FE}		Max.:240, Min.:15		Max.:240, Min.:15			Max.:180, Min.:7		
			(A~E: $V_{CE}=10V, I_C=5A$; F~H: $V_{CE}=10V, I_C=3A$)		(A~E: $V_{CE}=10V, I_C=7.5A$; F~H: $V_{CE}=10V, I_C=5A$)			(A~E: $V_{CE}=5V, I_C=0.5A$; F~H: $V_{CE}=5V, I_C=0.25A$)		
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 4 ($I_E=5mA$)		≥ 4 ($I_E=5mA$)					

 h_{FE} Colored:

Color	Red	Orange	Yellow	Green	Blue	Purple
h_{FE}	15~25	25~40	40~55	55~80	80~120	120~240

Outline and Dimensions: